Satoshi Yamasaki

List of Publications by Year
in descending order

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251 papers	5,822 citations	76196 40 h-index	118652 62 g-index
254 all docs	254 docs citations	254 times ranked	3794 citing authors

#	Article	IF	Citations
1	Optically detected magnetic resonance of nitrogen-vacancy centers in vertical diamond Schottky diodes. Japanese Journal of Applied Physics, 2022, 61, SC1061.	0.8	0
2	Selectively buried growth of heavily B doped diamond layers with step-free surfaces in N doped diamond (111) by homoepitaxial lateral growth. Applied Surface Science, 2022, , 153340.	3.1	1
3	Impact of nitrogen doping on homoepitaxial diamond (111) growth. Diamond and Related Materials, 2022, 125, 108997.	1.8	0
4	Study of ion-implanted nitrogen related defects in diamond Schottky barrier diode by transient photocapacitance and photoluminescence spectroscopy. Japanese Journal of Applied Physics, 2021, 60, SBBD07.	0.8	3
5	Carrier transport mechanism of diamond p⁺â€“n junction at low temperature using Schottkyâ€“pn junction structure. Japanese Journal of Applied Physics, 2021, 60, 030905.	0.8	5
6	Inversion channel MOSFET on heteroepitaxially grown free-standing diamond. Carbon, 2021, 175, 615-619.	5.4	9
7	Mechanical damage-free surface planarization of single-crystal diamond based on carbon solid solution into nickel. Diamond and Related Materials, 2021, 116, 108390.	1.8	1
8	Inversion-type p-channel diamond MOSFET issues. Journal of Materials Research, 2021, 36, 4688-4702.	1.2	13
9	Insight into temperature impact of Ta filaments on high-growth-rate diamond (100) films by hot-filament chemical vapor deposition. Diamond and Related Materials, 2021, 118, 108515.	1.8	8
10	Fabrication of inversion p-channel MOSFET with a nitrogen-doped diamond body. Applied Physics Letters, 2021, 119, .	1.5	11
11	Characterization of Schottky Barrier Diodes on Heteroepitaxial Diamond on 3C-SiC/Si Substrates. IEEE Transactions on Electron Devices, 2020, 67, 212-216.	1.6	11
12	Energy distribution of Al2O3/diamond interface states characterized by high temperature capacitance-voltage method. Carbon, 2020, 168, 659-664.	5.4	20
13	Vector Electrometry in a Wide-Gap-Semiconductor Device Using a Spin-Ensemble Quantum Sensor. Physical Review Applied, 2020, 14, .	1.5	17
14	Insight into Al2O3/B-doped diamond interface states with high-temperature conductance method. Applied Physics Letters, 2020, 117, .	1.5	11
15	Study of defects in diamond Schottky barrier diode by photocurrent spectroscopy. Japanese Journal of Applied Physics, 2020, 59, SGGK14.	0.8	2
16	Temperature dependence of diamond MOSFET transport properties. Japanese Journal of Applied Physics, 2020, 59, SGGD19.	0.8	4
17	Determination of Current Leakage Sites in Diamond pâ€“n Junction. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900243.	0.8	1
18	Highâ€Rate Growth of Singleâ€Crystalline Diamond (100) Films by Hotâ€Filament Chemical Vapor Deposition with Tantalum Filaments at 3000â€‰Â°C. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900244.	0.8	7

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19	Inversion channel mobility and interface state density of diamond MOSFET using N-type body with various phosphorus concentrations. Applied Physics Letters, 2019, 114, .	1.5	19
20	Conductive-probe atomic force microscopy and Kelvin-probe force microscopy characterization of OH-terminated diamond (111) surfaces with step-terrace structures. Japanese Journal of Applied Physics, 2019, 58, SIIB08.	0.8	5
21	Highâ€Rate Growth of Singleâ€Crystalline Diamond (100) Films by Hotâ€Filament Chemical Vapor Deposition with Tantalum Filaments at 3000â€‰Â°C. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1970071.	0.8	1
22	Charge-state control of ensemble of nitrogen vacancy centers by nâ€“iâ€“n diamond junctions. Applied Physics Express, 2018, 11, 033004.	1.1	10
23	Single crystal diamond membranes for nanoelectronics. Nanoscale, 2018, 10, 4028-4035.	2.8	27
24	Anisotropic diamond etching through thermochemical reaction between Ni and diamond in high-temperature water vapour. Scientific Reports, 2018, 8, 6687.	1.6	41
25	Direct observation of inversion capacitance in p-type diamond MOS capacitors with an electron injection layer. Japanese Journal of Applied Physics, 2018, 57, 04FR01.	0.8	14
26	Temperature dependence of electrical characteristics for diamond Schottky-pn diode in forward bias. Diamond and Related Materials, 2018, 85, 49-52.	1.8	11
27	Formation of atomically flat hydroxyl-terminated diamond (1â€¯1â€¯1) surfaces via water vapor annealing. Applied Surface Science, 2018, 458, 222-225.	3.1	23
28	Reverseâ€recovery of diamond pâ€iâ€n diodes. IET Power Electronics, 2018, 11, 695-699.	1.5	4
29	Direct Nanoscale Sensing of the Internal Electric Field in Operating Semiconductor Devices Using Single Electron Spins. ACS Nano, 2017, 11, 1238-1245.	7.3	82
30	Fabrication of graphene on atomically flat diamond (111) surfaces using nickel as a catalyst. Diamond and Related Materials, 2017, 75, 105-109.	1.8	22
31	Mechanism of anisotropic etching on diamond (111) surfaces by a hydrogen plasma treatment. Applied Surface Science, 2017, 422, 452-455.	3.1	22
32	Dynamic properties of diamond high voltage pâ€“iâ€“n diodes. Japanese Journal of Applied Physics, 2017, 56, 04CR14.	0.8	10
33	Diamond Schottky-pn diode using lightly nitrogen-doped layer. Diamond and Related Materials, 2017, 75, 152-154.	1.8	37
34	Estimation of Inductively Coupled Plasma Etching Damage of Boronâ€Doped Diamond Using Xâ€Ray Photoelectron Spectroscopy. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700233.	0.8	11
35	Observation of Interface Defects in Diamond Lateral p-n-Junction Diodes and Their Effect on Reverse Leakage Current. IEEE Transactions on Electron Devices, 2017, 64, 3298-3302.	1.6	6
36	High-Temperature Bipolar-Mode Operation of Normally-Off Diamond JFET. IEEE Journal of the Electron Devices Society, 2017, 5, 95-99.	1.2	27

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37	Influence of substrate misorientation on the surface morphology of homoepitaxial diamond (111) films. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2051-2055.	0.8	10
38	N-type control of single-crystal diamond films by ultra-lightly phosphorus doping. Applied Physics Letters, 2016, 109, .	1.5	49
39	Magnetic Resonance Imaging Bone Edema at Enrollment Predicts Rapid Radiographic Progression in Patients with Early RA: Results from the Nagasaki University Early Arthritis Cohort. Journal of Rheumatology, 2016, 43, 1278-1284.	1.0	14
40	Pure negatively charged state of the NV center in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math>-type diamond. Physical Review B, 2016, 93, .	1.1	77
41	Inversion channel diamond metal-oxide-semiconductor field-effect transistor with normally off characteristics. Scientific Reports, 2016, 6, 31585.	1.6	150
42	Diamond electronics. , 2016, , .		2
43	Normally-Off Diamond Junction Field-Effect Transistors With Submicrometer Channel. IEEE Electron Device Letters, 2016, 37, 209-211.	2.2	36
44	Desorption time of phosphorus during MPCVD growth of n-type (001) diamond. Diamond and Related Materials, 2016, 64, 208-212.	1.8	11
45	Heavily phosphorus-doped nano-crystalline diamond electrode for thermionic emission application. Diamond and Related Materials, 2016, 63, 165-168.	1.8	23
46	Defect luminescence in Diamond and GaN: towards single photon emitting devices. , 2016, , .		0
47	Potential profile evaluation of a diamond lateral pâ€“n junction diode using Kelvin probe force microscopy. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2589-2594.	0.8	1
48	Fabrication of diamond lateral pâ€“n junction diodes on (111) substrates. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2548-2552.	0.8	7
49	Electronic properties of diamond Schottky barrier diodes fabricated on silicon-based heteroepitaxially grown diamond substrates. Applied Physics Express, 2015, 8, 104103.	1.1	30
50	Upregulation of Thrombospondin 1 Expression in Synovial Tissues and Plasma of Rheumatoid Arthritis: Role of Transforming Growth Factor-Î²1 toward Fibroblast-like Synovial Cells. Journal of Rheumatology, 2015, 42, 943-947.	1.0	21
51	Electrical excitation of silicon-vacancy centers in single crystal diamond. Applied Physics Letters, 2015, 106, .	1.5	33
52	Germanium-Vacancy Single Color Centers in Diamond. Scientific Reports, 2015, 5, 12882.	1.6	251
53	Realization of Atomically Controlled Diamond Surfaces. Journal of the Japan Society for Precision Engineering, 2014, 80, 433-438.	0.0	0
54	Large improvement of phosphorus incorporation efficiency in n-type chemical vapor deposition of diamond. Applied Physics Letters, 2014, 105, .	1.5	23

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55	Atomistic mechanism of perfect alignment of nitrogen-vacancy centers in diamond. Applied Physics Letters, 2014, 105, .	1.5	39
56	Carrier transport in homoepitaxial diamond films with heavy phosphorus doping. Japanese Journal of Applied Physics, 2014, 53, 05FP05.	0.8	19
57	Observation of negative electron affinity in low-voltage discharging boron-doped polycrystalline diamond. Japanese Journal of Applied Physics, 2014, 53, 05FP09.	0.8	4
58	Generation and transportation mechanisms for two-dimensional hole gases in GaN/AlGaN/GaN double heterostructures. Journal of Applied Physics, 2014, 115, .	1.1	42
59	Direct first-principles simulation of a high-performance electron emitter: Lithium-oxide-coated diamond surface. Journal of Applied Physics, 2014, 116, .	1.1	6
60	Electron emission from nitrogen-containing diamond with narrow-gap coplanar electrodes. Japanese Journal of Applied Physics, 2014, 53, 05FP08.	0.8	0
61	Diamond electronic devices fabricated using heavily doped hopping p⁺and n⁺layers. Japanese Journal of Applied Physics, 2014, 53, 05FA12.	0.8	29
62	Investigation of electron emission site of pâ€“iâ€“n diode-type emitters with negative electron affinity. Japanese Journal of Applied Physics, 2014, 53, 05FP07.	0.8	0
63	Analysis of selective growth of n-type diamond in lateral pâ€“n junction diodes by cross-sectional transmission electron microscopy. Japanese Journal of Applied Physics, 2014, 53, 05FP01.	0.8	10
64	Polarizationâ€controlled dressedâ€photonâ€“phonon etching of patterned diamond structures. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 2339-2342.	0.8	7
65	Doping and interface of homoepitaxial diamond for electronic applications. MRS Bulletin, 2014, 39, 499-503.	1.7	49
66	Unique temperature dependence of deep ultraviolet emission intensity for diamond light emitting diodes. Japanese Journal of Applied Physics, 2014, 53, 05FP02.	0.8	4
67	600 V Diamond Junction Field-Effect Transistors Operated at 200$^{circ}{m C}$. IEEE Electron Device Letters, 2014, 35, 241-243.	2.2	74
68	Perfect selective alignment of nitrogen-vacancy centers in diamond. Applied Physics Express, 2014, 7, 055201.	1.1	84
69	Reduction of nâ€type diamond contact resistance by graphite electrode. Physica Status Solidi - Rapid Research Letters, 2014, 8, 137-140.	1.2	16
70	Energy-loss mechanism of single-crystal silicon microcantilever due to surface defects generated during plasma processing. Journal of Micromechanics and Microengineering, 2013, 23, 065020.	1.5	9
71	Electrical characterization of diamond Pi<scp>N</scp> diodes for high voltage applications. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 2035-2039.	0.8	52
72	Light penetration depth dependence of photocarrier life time and the Hall effect in phosphorous-doped and boron-doped homoepitaxial CVD diamond films. Diamond and Related Materials, 2013, 33, 49-53.	1.8	0

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73	Fabrication of bipolar junction transistor on (001)-oriented diamond by utilizing phosphorus-doped n-type diamond base. Diamond and Related Materials, 2013, 34, 41-44.	1.8	38
74	Single photon, spin, and charge in diamond semiconductor at room temperature. , 2013, , .		0
75	Early diagnosis and treatment for remission of clinically amyopathic dermatomyositis complicated by rapid progress interstitial lung disease: a report of two cases. Modern Rheumatology, 2013, 23, 190-194.	0.9	21
76	Diamond foam electrodes for electrochemical applications. Electrochemistry Communications, 2013, 33, 88-91.	2.3	57
77	Tunable light emission from nitrogen-vacancy centers in single crystal diamond PIN diodes. Applied Physics Letters, 2013, 102, .	1.5	62
78	Ab initio dynamics of field emission from diamond surfaces. Applied Physics Letters, 2013, 103, .	1.5	8
79	High-Temperature Operation of Diamond Junction Field-Effect Transistors With Lateral p-n Junctions. IEEE Electron Device Letters, 2013, 34, 1175-1177.	2.2	51
80	Takayasu arteritis developing during treatment of ulcerative colitis with infliximab. Modern Rheumatology, 2013, 23, 572-576.	0.9	6
81	An elderly patient with chronic active Epsteinâ€“Barr virus infection with mixed cryoglobulinemia and review of the literature. Modern Rheumatology, 2013, 23, 1022-1028.	0.9	4
82	High-Voltage Vacuum Switch with a Diamond pâ€“iâ€“n Diode Using Negative Electron Affinity. Japanese Journal of Applied Physics, 2012, 51, 090113.	0.8	17
83	High serum matrix metalloproteinase 3 is characteristic of patients with paraneoplastic remitting seronegative symmetrical synovitis with pitting edema syndrome. Modern Rheumatology, 2012, 22, 584-588.	0.9	35
84	Unique Properties of Diamond and Its Device Applications. Hyomen Kagaku, 2012, 33, 634-638.	0.0	0
85	Isotope Effect of Deuterium Microwave Plasmas on the Formation of Atomically Flat (111) Diamond Surfaces. Japanese Journal of Applied Physics, 2012, 51, 090106.	0.8	4
86	Formation of Step-Free Surfaces on Diamond (111) Mesas by Homoepitaxial Lateral Growth. Japanese Journal of Applied Physics, 2012, 51, 090107.	0.8	19
87	Diamond bipolar junction transistor device with phosphorus-doped diamond base layer. Diamond and Related Materials, 2012, 27-28, 19-22.	1.8	51
88	Device Design of Diamond Schottky-pn Diode for Low-Loss Power Electronics. Japanese Journal of Applied Physics, 2012, 51, 090116.	0.8	6
89	Nonlinear behavior of currentâ€dependent emission for diamond lightâ€emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1754-1760.	0.8	13
90	Diamond Junction Field-Effect Transistors with Selectively Grown n^{+}-Side Gates. Applied Physics Express, 2012, 5, 091301.	1.1	61

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91	Maskless Selective Growth Method for pâ€“n Junction Applications on (001)-Oriented Diamond. Japanese Journal of Applied Physics, 2012, 51, 090118.	0.8	6
92	Electrical properties of lateral pâ€“n junction diodes fabricated by selective growth of n⁺ diamond. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1761-1764.	0.8	32
93	Isotope Effect of Deuterium Microwave Plasmas on the Formation of Atomically Flat (111) Diamond Surfaces. Japanese Journal of Applied Physics, 2012, 51, 090106.	0.8	2
94	Formation of Step-Free Surfaces on Diamond (111) Mesas by Homoepitaxial Lateral Growth. Japanese Journal of Applied Physics, 2012, 51, 090107.	0.8	19
95	High-Voltage Vacuum Switch with a Diamond pâ€“iâ€“n Diode Using Negative Electron Affinity. Japanese Journal of Applied Physics, 2012, 51, 090113.	0.8	22
96	Device Design of Diamond Schottky-pn Diode for Low-Loss Power Electronics. Japanese Journal of Applied Physics, 2012, 51, 090116.	0.8	5
97	Maskless Selective Growth Method for pâ€“n Junction Applications on (001)-Oriented Diamond. Japanese Journal of Applied Physics, 2012, 51, 090118.	0.8	5
98	Disease activity score 28 may overestimate the remission induction of rheumatoid arthritis patients treated with tocilizumab: comparison with the remission by the clinical disease activity index. Modern Rheumatology, 2011, 21, 365-369.	0.9	27
99	Reduction in serum levels of substance P in patients with rheumatoid arthritis by etanercept, a tumor necrosis factor inhibitor. Modern Rheumatology, 2011, 21, 244-250.	0.9	17
100	Energy level of compensator states in (001) phosphorus-doped diamond. Diamond and Related Materials, 2011, 20, 1016-1019.	1.8	20
101	Multiple phosphorus chemical sites in heavily phosphorus-doped diamond. Applied Physics Letters, 2011, 98, .	1.5	16
102	Cageâ€Shaped Borate Esters with Tris(2â€oxyphenyl)methane or â€silane System Frameworks Bearing Multiple Tuning Factors: Geometric and Substituent Effects on Their Lewis Acid Properties. Chemistry - A European Journal, 2011, 17, 3856-3867.	1.7	26
103	Effects of the anti-interleukin-6 receptor antibody, tocilizumab, on serum lipid levels in patients with rheumatoid arthritis. Rheumatology International, 2011, 31, 451-456.	1.5	100
104	Carrier transport of diamond p⁺â€iâ€n⁺ junction diode fabricated using lowâ€resistance hopping p⁺ and n⁺ layers. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 937-942.	0.8	5
105	Misorientation-angle dependence of boron incorporation into (001)-oriented chemical-vapor-deposited (CVD) diamond. Journal of Crystal Growth, 2011, 317, 60-63.	0.7	90
106	CD4+CD25^{high}CD127^{low/-} Treg Cell Frequency from Peripheral Blood Correlates with Disease Activity in Patients with Rheumatoid Arthritis. Journal of Rheumatology, 2011, 38, 2517-2521.	1.0	74
107	Enhancement in emission efficiency of diamond deep-ultraviolet light emitting diode. Applied Physics Letters, 2011, 99, .	1.5	73
108	A case of SjÃ¶gren syndrome with pulmonary amyloidosis complicating microscopic polyangiitis. Modern Rheumatology, 2011, 21, 646-650.	0.9	3

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109	In rheumatoid arthritis patients treated with tocilizumab, the rate of clinical disease activity index (CDAI) remission at 24 weeks is superior in those with higher titers of IgM-rheumatoid factor at baseline. Modern Rheumatology, 2011, 21, 370-374.	0.9	16
110	Contribution of an adenine to guanine single nucleotide polymorphism of the matrix metalloproteinase-13 (MMP-13) â^'77 promoter region to the production of anticyclic citrullinated peptide antibodies in patients with HLA-DRB1*shared epitope-negative rheumatoid arthritis. Modern Rheumatology, 2011, 21, 240-243.	0.9	1
111	Disease activity score 28 may overestimate the remission induction of rheumatoid arthritis patients treated with tocilizumab: comparison with the remission by the clinical disease activity index. Modern Rheumatology, 2011, 21, 365-369.	0.9	14
112	Cutaneous vasculitis induced by TNF inhibitors: a report of three cases. Modern Rheumatology, 2010, 20, 86-89.	0.9	37
113	Switching to the anti-interleukin-6 receptor antibody tocilizumab in rheumatoid arthritis patients refractory to antitumor necrosis factor biologics. Modern Rheumatology, 2010, 20, 40-45.	0.9	11
114	Improvement of (001)-oriented diamond p-i-n diode by use of selective grown n+ layer. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 2099-2104.	0.8	12
115	Diamond Schottkyâ€pn diode without tradeâ€off relationship between onâ€resistance and blocking voltage. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 2105-2109.	0.8	34
116	Electron Emission from a Diamond (111) pâ€“iâ€“n+Junction Diode with Negative Electron Affinity during Room Temperature Operation. Applied Physics Express, 2010, 3, 041301.	1.1	24
117	Plasma-Induced Deterioration of Mechanical Characteristics of Microcantilever. Japanese Journal of Applied Physics, 2010, 49, 04DL20.	0.8	16
118	High-Performance Three-Terminal Fin Field-Effect Transistors Fabricated by a Combination of Damage-Free Neutral-Beam Etching and Neutral-Beam Oxidation. Japanese Journal of Applied Physics, 2010, 49, 04DC17.	0.8	11
119	Growth of atomically step-free surface on diamond {111} mesas. Diamond and Related Materials, 2010, 19, 288-290.	1.8	33
120	Mechanism of mechanical deterioration in silicon microcantilever induced by plasma process. , 2010, , .		0
121	Switching to the anti-interleukin-6 receptor antibody tocilizumab in rheumatoid arthritis patients refractory to antitumor necrosis factor biologics. Modern Rheumatology, 2010, 20, 40-45.	0.9	13
122	Electron Emission from Diamond (111) p+-i-n+ Junction Diode. Materials Research Society Symposia Proceedings, 2009, 1203, 1.	0.1	0
123	Prediction of DAS28-CRP remission in patients with rheumatoid arthritis treated with tacrolimus at 6 months by baseline variables. Modern Rheumatology, 2009, 19, 652-656.	0.9	6
124	Prediction of DAS28-ESR remission at 6 months by baseline variables in patients with rheumatoid arthritis treated with etanercept in Japanese population. Modern Rheumatology, 2009, 19, 488-492.	0.9	20
125	Diamond Schottky pâ€“n diode with high forward current density. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2086-2090.	0.8	20
126	Diamond Schottky-pn diode with high forward current density and fast switching operation. Applied Physics Letters, 2009, 94, .	1.5	77

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127	Flattening of oxidized diamond (111) surfaces with H2SO4/H2O2 solutions. Diamond and Related Materials, 2009, 18, 213-215.	1.8	12
128	Selective Growth of Buried n+Diamond on (001) Phosphorus-Doped n-Type Diamond Film. Applied Physics Express, 2009, 2, 055502.	1.1	55
129	Development of Low-AC-Loss Bi-2223 Superconducting Multifilamentary Wires. IEEE Transactions on Applied Superconductivity, 2009, 19, 3053-3056.	1.1	11
130	Electrical and light-emitting properties from (111)-oriented homoepitaxial diamond pâ€“iâ€“n junctions. Diamond and Related Materials, 2009, 18, 764-767.	1.8	18
131	Characterization of specific contact resistance on heavily phosphorus-doped diamond films. Diamond and Related Materials, 2009, 18, 782-785.	1.8	35
132	Hall effect of photocurrent in CVD diamond film. Diamond and Related Materials, 2009, 18, 779-781.	1.8	2
133	High performance of diamond p+-i-n+ junction diode fabricated using heavily doped p+ and n+ layers. Applied Physics Letters, 2009, 94, .	1.5	73
134	Prediction of DAS28-ESR remission at 6Âmonths by baseline variables in patients with rheumatoid arthritis treated with etanercept in Japanese population. Modern Rheumatology, 2009, 19, 488-492.	0.9	19
135	Electrical and lightâ€emitting properties of homoepitaxial diamond pâ€“iâ€“n junction. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2200-2206.	0.8	29
136	Electrical activity of doped phosphorus atoms in (001) nâ€type diamond. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2195-2199.	0.8	29
137	Fermi level pinning-free interface at metals/homoepitaxial diamond (111) films after oxidation treatments. Applied Physics Letters, 2008, 92, 112112.	1.5	14
138	Homoepitaxial diamond pâ€“n+ junction with low specific on-resistance and ideal built-in potential. Diamond and Related Materials, 2008, 17, 782-785.	1.8	23
139	Low specific contact resistance of heavily phosphorus-doped diamond film. Applied Physics Letters, 2008, 93, .	1.5	68
140	Atomically flat diamond (111) surface formation by homoepitaxial lateral growth. Diamond and Related Materials, 2008, 17, 1051-1054.	1.8	43
141	Roughening of atomically flat diamond (111) surfaces by a hot HNO3/H2SO4 solution. Diamond and Related Materials, 2008, 17, 486-488.	1.8	14
142	Mapping of extended defects in B-doped (001) homoepitaxial diamond films by electron-beam-induced current (EBIC) and cathodoluminescence (CL) combination technique. Diamond and Related Materials, 2008, 17, 489-493.	1.8	5
143	Generation and reduction in SiO2/Si interface state density during plasma etching processes. Journal of Applied Physics, 2008, 104, 063308.	1.1	14
144	Exciton-derived Electron Emission from (001) Diamondpâ€“nJunction Diodes with Negative Electron Affinity. Applied Physics Express, 2008, 1, 015004.	1.1	8

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145	Total Photoelectron Emission Yield Spectroscopy on Diamond Surfaces. Hyomen Kagaku, 2008, 29, 151-158.	0.0	0
146	n-Type Diamond Growth by Phosphorus Doping. Materials Research Society Symposia Proceedings, 2007, 1039, 1.	0.1	2
147	Low-damage fabrication of high aspect nanocolumns by using neutral beams and ferritin-iron-core mask. Journal of Vacuum Science & Technology B, 2007, 25, 760.	1.3	11
148	Hillock-Free Heavily Boron-Doped Homoepitaxial Diamond Films on Misoriented (001) Substrates. Japanese Journal of Applied Physics, 2007, 46, 1469-1470.	0.8	28
149	Etching Damage in Diamond Studied Using an Energy-Controlled Oxygen Ion Beam. Japanese Journal of Applied Physics, 2007, 46, 60-64.	0.8	9
150	Surface roughening of diamond (001) films during homoepitaxial growth in heavy boron doping. Diamond and Related Materials, 2007, 16, 767-770.	1.8	37
151	Electrical and light-emitting properties of (001)-oriented homoepitaxial diamond pâ€“îâ€“n junction. Diamond and Related Materials, 2007, 16, 1025-1028.	1.8	18
152	Surface electronic properties on boron doped (111) CVD homoepitaxial diamond films after oxidation treatments. Diamond and Related Materials, 2007, 16, 831-835.	1.8	6
153	The role of boron atoms in heavily boron-doped semiconducting homoepitaxial diamond growth â€” Study of surface morphology. Diamond and Related Materials, 2007, 16, 409-411.	1.8	11
154	Carrier compensation in (001) n-type diamond by phosphorus doping. Diamond and Related Materials, 2007, 16, 796-799.	1.8	40
155	n-type diamond growth by phosphorus doping on (0â€‰0â€‰1)-oriented surface. Journal Physics D: Applied Physics, 2007, 40, 6189-6200.	1.3	90
156	Growth and characterization of boron-doped CVD homoepitaxial diamond films. Journal of Crystal Growth, 2007, 299, 235-242.	0.7	4
157	Electrical and optical characterizations of (001)-oriented homoepitaxial diamond pâ€“n junction. Diamond and Related Materials, 2006, 15, 513-516.	1.8	15
158	N-type doping on (001)-oriented diamond. Diamond and Related Materials, 2006, 15, 548-553.	1.8	20
159	Surface conductive layers on (111) diamonds after oxygen treatments. Diamond and Related Materials, 2006, 15, 692-697.	1.8	20
160	Cage-Shaped Borate Esters with Enhanced Lewis Acidity and Catalytic Activity. Organic Letters, 2006, 8, 761-764.	2.4	40
161	Ab initio energetics of phosphorus impurity in subsurface regions of hydrogenated diamond surfaces. E-Journal of Surface Science and Nanotechnology, 2006, 4, 124-128.	0.1	5
162	Emission properties from dense exciton gases in diamond. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 3226-3244.	0.8	21

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163	Ab initio energetics of phosphorus related complex defects in synthetic diamond. Physica B: Condensed Matter, 2006, 376-377, 304-306.	1.3	16
164	Hydrogen plasma etching mechanism on (001) diamond. Journal of Crystal Growth, 2006, 293, 311-317.	0.7	24
165	Energetics of dopant atoms in subsurface positions of diamond semiconductor. Superlattices and Microstructures, 2006, 40, 574-579.	1.4	4
166	High-Efficiency Excitonic Emission with Deep-Ultraviolet Light from (001)-Oriented Diamondp-i-nJunction. Japanese Journal of Applied Physics, 2006, 45, L1042-L1044.	0.8	52
167	Photoelectron Emission Mechanism From Hydrogen Terminated Nano-Crystalline Diamond. Materials Research Society Symposia Proceedings, 2006, 956, 1.	0.1	3
168	Surface reactions during etching of organic low-k films by plasmas of N2 and H2. Journal of Applied Physics, 2006, 99, 083305.	1.1	40
169	Thermodynamic theory for efficiency of multiple impurity-atom doping in diamond. Physica Status Solidi A, 2005, 202, 2134-2140.	1.7	4
170	Growth and characterization of phosphorus-doped diamond using organophosphorus gases. Physica Status Solidi A, 2005, 202, 2122-2128.	1.7	22
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